NSN 5961-01-624-7504

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Overall Length:

Between 1.335 inches and 1.345 inches

Overall Height:

Between 0.125 inches and 0.170 inches

Overall Width:

Between 0.380 inches and 0.390 inches

Function For Which Designed:

Programmable transistor

Internal Configuration:

Field effect

Electrode Internally-electrically Connected To Case:

Gate

Features Provided:

Gold plated leads

Voltage Rating In Volts Per Characteristic:

65.0 drain to source voltage

Current Rating Per Characteristic:

10.0 microamperes zero-gate-voltage drain current

Power Rating Per Characteristic:

298.0 watts total device dissipation

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Product Name:

Rf power field effect transistor

Special Features:

In tape and reel, r3 suffix= 250 units per 56mm, 13 inch reel; rohs compliant; designed for gsm and gsm edge base station applications with frequencies from 921 to 960 mhz; designed for maximum gain and instertion phase flatness; high gain and broadband performance of these devices make them ideal for large signal, common source amplifier applications in 28 volt base stations; high efficiency; high linearity; integrated esd protection

Terminal Type And Quantity:

3 pin

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

A110a0